


U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT		Docket Number 2345/209	
Application Number Unassigned 10/541480	Filing Date Herewith	Examiner Unassigned	Art Unit Unassigned
Title INCREASING THE RESISTANCE OF CRYSTALS TO OPTICAL DAMAGE		Applicant(s) Karsten BUSE et al.	

Commissioner for Patents
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1. In accordance with the duty of disclosure under 37 C.F.R. § 1.56 and in conformance with the procedures of 37 C.F.R. §§ 1.97 and 1.98 and M.P.E.P. § 609, attorneys for Applicants hereby bring the reference(s) listed on the attached modified PTO form 1449 to the attention of the Examiner. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom.
2. A copy of each patent, publication or other information listed on the modified PTO form 1449 is enclosed, except as otherwise indicated.

Dated: July 5, 2005

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT PTO-1449	ATTY. DOCKET NO. 2345/209	SERIAL NO. 10/541480 <small>Unassigned</small>
	APPLICANT Karsten BUSE et al.	
	FILING DATE Herewith	GROUP Unassigned

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	PATENT NUMBER	PATENT DATE	INVENTOR NAME(S)
	* US 2002/088966 A1	July 11, 2002	Harold Stoll

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DISCLOSURE DATE	COUNTRY	TRANSLATION
	* EP 0 824 217 A	February 18, 1998	Europe	n/a

*Cited by International Searching Authority (copy to be provided by International Searching Authority to the U.S. Patent Office)

OTHER DOCUMENTS

EXAMINER INITIAL	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
	* Kamber N Y et al.; "Threshold effect of incident light intensity for the resistance against the photorefractive light-induced scattering in doped lithium niobate crystals," Optics Communications, North-Holland Publishing Co., Amsterdam, NL, vol. 176, no. 1-3, March 2000, pages 91-96.
	* Buse K et al.; "Development of thermally fixed holograms in photorefractive lithium-niobate crystals without light," Optical Materials, Elsevier Science Publishers B.V., Amsterdam, NL, vol. 18, no. 1, October 2001, pages 17-18.
	* Galambos, L et al.; "Doubly doped stoichiometric and congruent lithium niobate for holographic data storage," Journal of Crystal Growth, North-Holland Publishing Co., Amsterdam, NL, vol. 229, no. 1-4, July 2001, pages 228-232.
	* Patent Abstracts of Japan, vol. 0174, no. 52 (C-1099), August 19, 1993, & JP 5 105594 A, April 27, 1993.
	* Patent Abstracts of Japan, vol. 0180, no. 46 (C-1157), January 25, 1994, & JP 5 270992 A, October 19, 1993.
	* Patent Abstracts of Japan, vol. 0174, no. 52 (C-1099), August 19, 1993, & JP 5 105593 A, April 27, 1993.
	* Patent Abstracts of Japan, vol. 0174, no. 52 (C-1099), August 19, 1993, & JP 5 105590 A, April 27, 1993.
	* Zhang, Y et al; "Growth and properties of Zn doped lithium niobate crystal," Journal of Crystal Growth, Northern Holland Publishing, Amsterdam, NL, vol. 233, no. 3, December 2001.

EXAMINER EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	DATE CONSIDERED
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